

wherein:

R represents a linkage group; and

each X is individually selected from the group consisting of hydrogen, the halogens, nitro groups, amino groups, acetamido groups, substituted and unsubstituted cyclic and heterocyclic groups, and COR¹, where R¹ is selected from the group consisting of hydrogen, substituted and unsubstituted phenyl groups, substituted and unsubstituted alkyl groups, cinnamoyl, naphthoyl, acryloyl, methacryloyl, furoyl, and thiophenecarbonyl groups; and

subjecting said antireflective compound to a chemical vapor deposition process so as to deposit said antireflective compound in a layer on said substrate surface, said antireflective compound layer deposited on said substrate surface absorbing at least about 90% of light at a wavelength of from about 150-500 nm.

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13. (Amended) The method of claim 2, wherein said antireflective compound layer has a thickness after said depositing step, and said thickness will change by less than about 10% in solvents utilized in said photoresist layer.

C2 14. (Amended) The method of claim 1, further including the steps of:
exposing at least a portion of said photoresist layer to activating radiation;
developing said exposed photoresist layer; and
subjecting said exposed photoresist layer to an etching process.

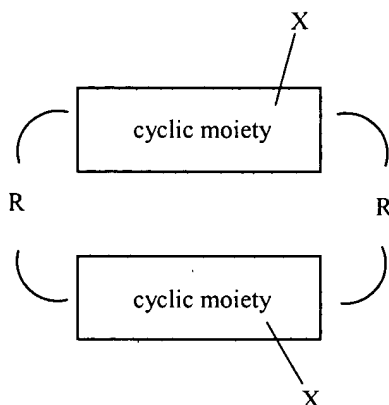
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Please cancel claim 15.

19. (Amended) A precursor structure formed during the course of the integrated circuit manufacturing process, said structure comprising:

a substrate having a surface; and

C3 a layer comprising an antireflective compound on said surface, said antireflective compound layer being formed on said surface by a chemical vapor deposition process and said antireflective compound comprising a polymer being formed from monomers having the formula

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wherein:

R represents a linkage group; and

C₃ each X is individually selected from the group consisting of the hydrogen, the halogens, nitro groups, amino groups, acetamido groups, substituted and unsubstituted cyclic and heterocyclic groups, and COR¹, where R¹ is selected from the group consisting of hydrogen, substituted and unsubstituted phenyl groups, substituted and unsubstituted alkyl groups, cinnamoyl, naphthoyl, acryloyl, methacryloyl, furoyl, and thiophenecarbonyl groups, wherein the antireflective compound layer absorbs at least about 90% of light at a wavelength of from about 150-500 nm.

C₄ 26. (Amended) The structure of claim 20, wherein said antireflective compound layer has a thickness, and said thickness will change by less than about 10% in solvents utilized in said photoresist layer

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Please cancel claim 27.

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